

Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO.	SERIAL NO.
		0057-2534-2YY DIV	New Application
		APPLICANT	GROUP 2823
		Shuichi UENO, et al.	
LIST OF REFERENCES CITED BY APPLICANT (Use Several Sheets if Necessary)		FILING DATE HEREWITH	

JC615 U.S. PTO
09/429281
10/28/99

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	NO
G	AL	4-157766	5/29/92	JAPAN		XX
G	AM	7-176743	7/14/95	JAPAN		XX
	AN					
	AO					
	AP					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

G	AR	C. KUO, "EMBEDDED FLASH MEMORY APPLICATIONS, TECHNOLOGY AND DESIGN", 1995 IEDM SHORT COURSE, Motorola Inc., Austin, Texas, 1995.
	AS	
	AT	

EXAMINER FOURSO~ DATE CONSIDERED 6/17/00

*EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw Line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 0057-2534-2YY	SERIAL NO. 09/429,283
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT		Shuichi UENO, et al.	
		FILING DATE		GROUP	
		October 28, 1999		2811 2823	
U.S. PATENT DOCUMENTS					
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS
	AA	5,514,902	05/07/96	Y. KAWASAKI, et al.	—
	AB	5,567,638	10/22/96	Y.-H. LIN, et al.	—
	AC	5,607,868	03/04/97	N. CHIDA, et al.	
	AD				
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	AI				
	AJ				
	AK				
	AL				
	AM				
	AN				
FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
	AO	4-157766	05/29/92	JAPAN (with English Abstract)	— X
	AP				
	AQ				
	AR				
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	AU				
	AV				
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)					
	AW	T. KUROI, et al., Japanese Journal of Applied Physics, Vol. 34, No. 2B, pps. 771-775, "THE IMPACT OF NITROGEN IMPLANTATION INTO HIGHLY DOPED POLYSILICON GATES OF HIGHLY RELIABLE AND HIGH-PERFORMANCE SUB-QUARTER-MICRON DUAL-GATE COMPLEMENTARY METAL OXIDE SEMICONDUCTOR," February 1, 1995			
	AX	A.I. CHOU et al., 1997 IEEE INTERNATIONAL RELIABILITY PHYSICS SYMPOSIUM PROCEEDINGS, Vol. SYMP. 35, pps. 174-177, "THE EFFECTS OF NITROGEN IMPLANT INTO GATE ELECTRODE ON THE CHARACTERISTICS OF DUAL-GATE MOSFETS WITH ULTRA-THIN OXIDE AND OXYNITRIDES," 1997			
	AY				
	AZ				
Examiner	FOURSON			Date Considered	6/17/00
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					